

KP 2000A 1800~2200V

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

- AC controllers
- DC and AC motor control
- Controlled rectifiers

$I_{T(AV)}$	2000 A
V_{DRM}/V_{RRM}	1800V
I_{TSM}	38 kA
I^2t	7220 $10^3 A^2S$

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T _J (°C)	VALUE			UNIT
					Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T _C =70°C	125	2000		2670	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms		125	1800		2200	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}		125			160	mA
I _{TSM}	Surge on-state current	10ms half sine wave		125			38	kA
I ² t	I ² t for fusing coordination	V _R =0.6V _{RRM}					7220	A ² s*10 ³
V _{TO}	Threshold voltage			125			0.80	V
r _T	On-state slope resistance						0.14	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =5000A, F=35kN		25			2.00	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =0.67V _{DRM}		125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V _{DM} = 67%V _{DRM} to 3000A, Gate pulse t _r ≤0.5μs I _{GM} =1.5A		125			250	A/μs
Q _{rr}	Recovery charge	I _{TM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V		125		2000		μC
I _{GT}	Gate trigger current	V _A =12V, I _A =1A		25	40		300	mA
V _{GT}	Gate trigger voltage				0.8		3.0	V
I _H	Holding current				20		300	mA
V _{GD}	Non-trigger gate voltage	V _{DM} =67%V _{DRM}		125	0.3			V
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 35.0kN					0.012	°C /W
R _{th(c-h)}	Thermal resistance case to heatsink						0.003	
F _m	Mounting force				30		40	kN
T _{stg}	Stored temperature				-40		140	°C
W _t	Weight					880		g
Outline	Ø100xØ63x26 mm							

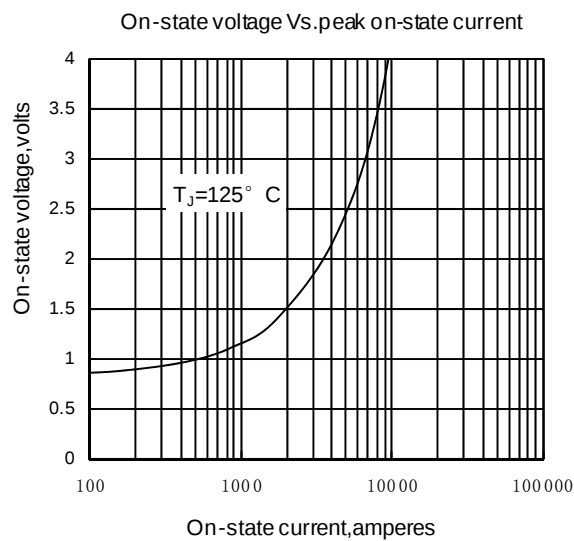


Fig1

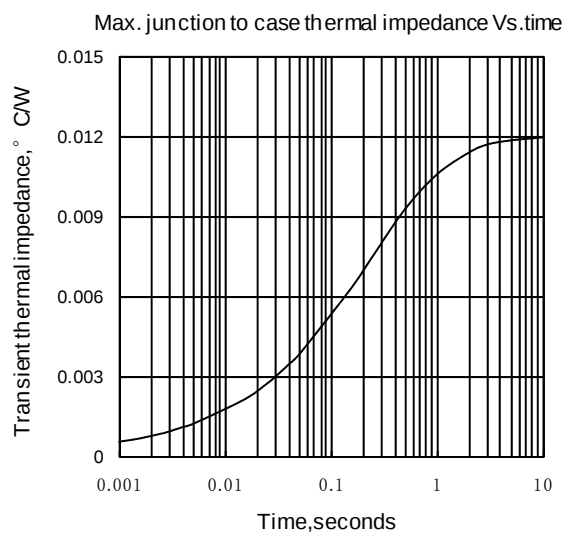


Fig2

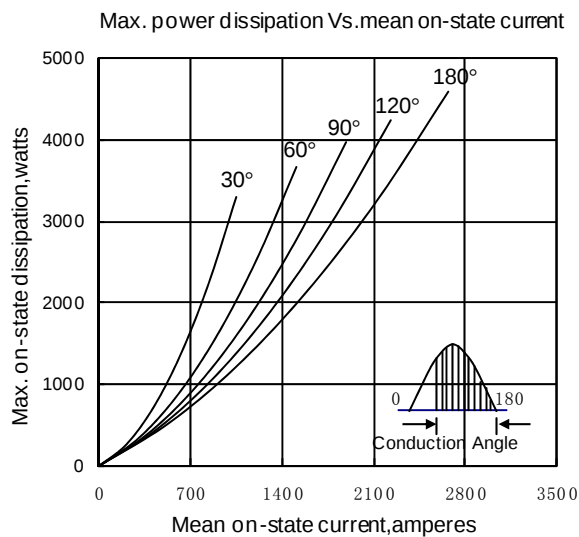


Fig3

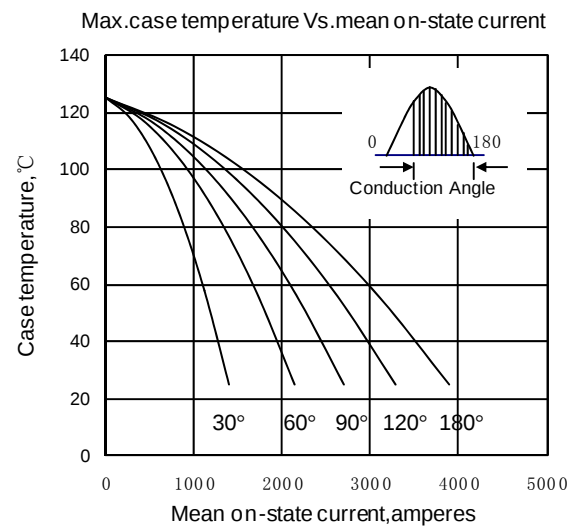


Fig4

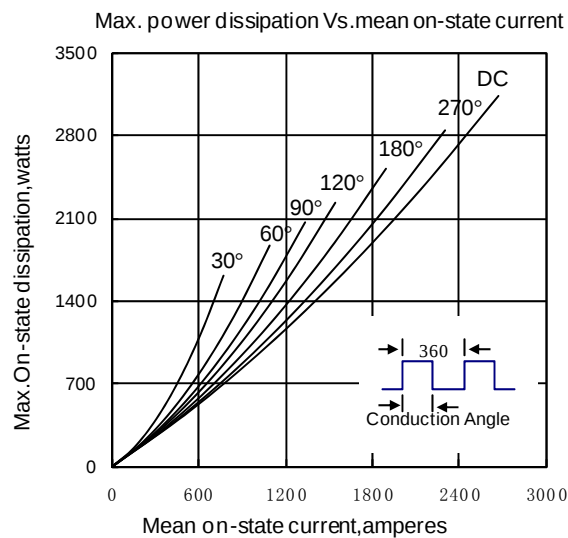


Fig5

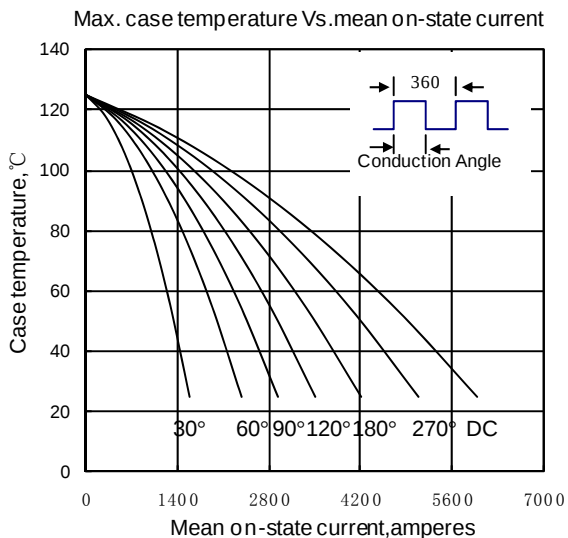


Fig6

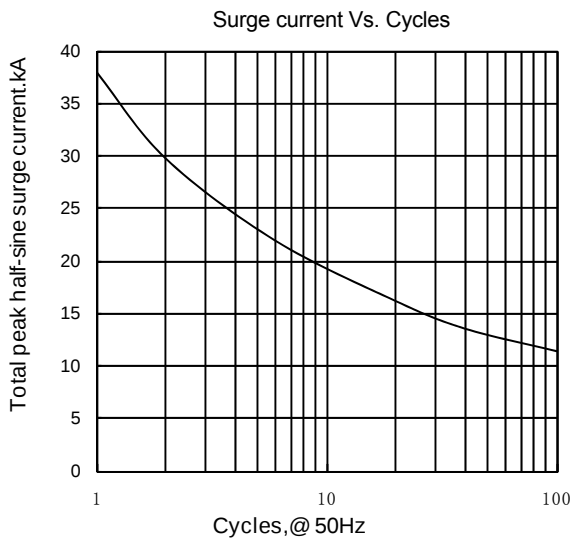


Fig7

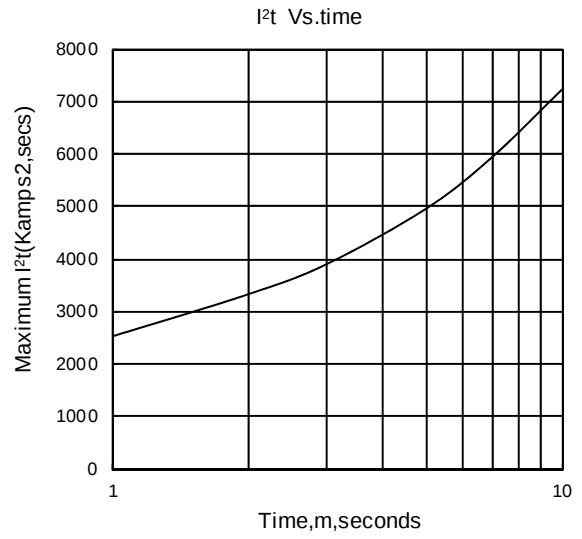


Fig8

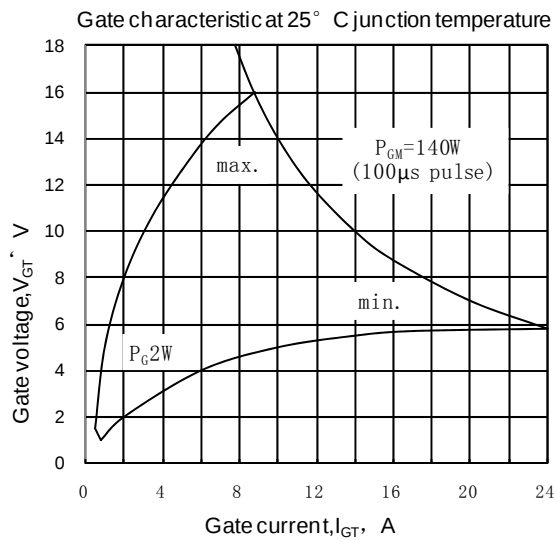


Fig9

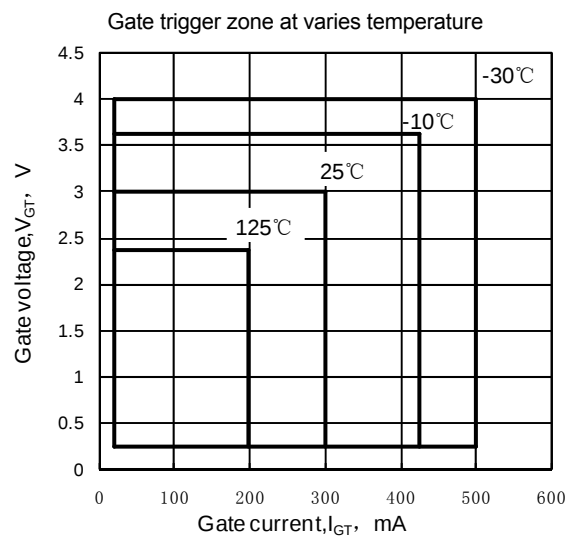


Fig10

Outline:

